



THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicants : Rhodes et al.
Serial No. : 09/008,531
Filed : January 16, 1998
Title : METHOD OF MAKING A SEMICONDUCTOR DEVICE HAVING
IMPROVED CONTACTS
Docket No. : MIO0012V2
Examiner : Eaton
Art Unit : 2823

Assistant Commissioner for Patents
Washington, DC 20231

CERTIFICATE OF MAILING
I hereby certify that this correspondence is being deposited with the
United States Postal Service as first class mail in an envelope addressed
to: Assistant Commissioner for Patents, Washington, D.C. 20231, on
September 24, 2001.

Julie G. Cope
Julie G. Cope Reg. No. 48,624

Sir:

AMENDMENT

This paper is being filed in response to the Office Action mailed July 18, 2001.

Reconsideration and reexamination are respectfully requested in light of the remarks below.

CLEAN VERSION OF THE AMENDMENTS

(A marked-up version of the amendments is found in the Appendix)

IN THE CLAIMS

26. A process for making a semiconductor device having an improved contact to a
conductive layer comprising the steps of:

providing a first layer of material and forming an opening therein, said opening including
sidewalls;

forming a layer of a first conductive material on said first layer of material and along the
surfaces of said sidewalls of said opening to form a localized thick region;

forming an overlayer of material on said layer of said first conductive material;

etching a contact hole in said overlayer and an overetch amount of said layer of said first
conductive material, wherein said overetch amount is an amount necessary to account for
variations in the thickness of said overlayer in forming said first layer of material and said layer
of said first conductive material; and